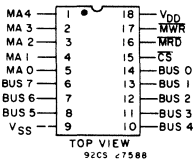


# CDP1824, CDP1824C

## 32-Word x 8-Bit Static Random-Access Memory



Terminal Assignment

**Features:**

- Access time:  
710 ns at  $V_{DD}=5\text{ V}$ ,  
320 ns at  $V_{DD}=10\text{ V}$
- No precharge or clock required

The RCA-CDP1824 and CDP1824C types are 32-word x 8-bit fully static CMOS random-access memories for use in CDP1800 series microprocessor systems. These parts are compatible with the CDP1802 microprocessor and will interface directly without additional components.

The CDP1824 is fully decoded and does not require a precharge or clocking signal for proper operation. It has common input and output and is operated from a single voltage supply. The MRD signal (output disable control)

enables the three-state output drivers, and overrides the MWR signal. A CS input is provided for memory expansion.

The CDP1824C is functionally identical to the CDP1824. The CDP1824 has an operating range of 4 to 10.5 volts, and the CDP1824C has an operating voltage range of 4 to 6.5 volts. The CDP1824 and CDP1824C types are supplied in 18-lead hermetic dual-in-line ceramic packages (D suffix) and in 18-lead dual-in-line plastic packages (E suffix).

**OPERATIONAL MODES**

Function	$\overline{\text{CS}}$	$\overline{\text{MRD}}$	$\overline{\text{MWR}}$	Data Pins Status
READ	0	0	X	Output: High/Low Dependent on Data
WRITE	0	1	0	Input: Output Disabled
Not Selected	1	X	X	Output Disabled: High-Impedance State
Standby	0	1	1	

Logic 1 = High    Logic 0 = Low    X = Don't Care

**MAXIMUM RATINGS, Absolute-Maximum Values:**

DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )

(All voltage values referenced to  $V_{SS}$  terminal)

CDP1824	-0.5 to +11 V
CDP1824C	-0.5 to +7 V

INPUT VOLTAGE RANGE, ALL INPUTS

-0.5 to  $V_{DD} + 0.5\text{ V}$

DC INPUT CURRENT, ANY ONE INPUT

$\pm 10\text{ mA}$

OPERATING-TEMPERATURE RANGE ( $T_A$ ).

CERAMIC PACKAGES (D SUFFIX TYPES) . . . . . -55 to +125°C

PLASTIC PACKAGES (E SUFFIX TYPES) . . . . . -40 to +85°C

STORAGE TEMPERATURE RANGE ( $T_{stg}$ ) . . . . . -65 to +150°C

LEAD TEMPERATURE (DURING SOLDERING)

At distance  $1/16 \pm 1/32$  inch ( $1.59 \pm 0.79\text{ mm}$ ) from case for 10 s max. . . . . +265°C

# CDP1824, CDP1824C

OPERATING CONDITIONS at  $T_A$  = Full Package-Temperature Range

For maximum reliability, operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	CONDITIONS  $V_{DD}$ (V)	LIMITS				UNITS
		CDP1824D CDP1824E		CDP1824CD CDP1824CE		
		Min.	Max.	Min.	Max.	
Supply-Voltage Range	—	4	10.5	4	6.5	V
Recommended Input Voltage Range	—	$V_{SS}$	$V_{DD}$	$V_{SS}$	$V_{DD}$	V
Input Signal Rise or Fall Time, $t_r, t_f$	5	—	5	—	5	$\mu s$
	10	—	2	—	—	

▲ Input signal rise or fall times longer than these maxima can cause loss of stored data in either the selected or deselected mode.

## STATIC ELECTRICAL CHARACTERISTICS at $T_A = -40$ to $+85^\circ C$ , Except as noted

CHARACTERISTICS	TEST CONDITIONS			LIMITS						UNITS
	$V_O$ (V)	$V_{IN}$ (V)	$V_{DD}$ (V)	CDP1824			CDP1824C			
				Min.	Typ.*	Max.	Min.	Typ.*	Max.	
Quiescent Device Current, $I_{DD}$	—	—	5	—	25	50	—	100	200	$\mu A$
	—	—	10	—	250	500	—	—	—	
Output Voltage:	—	0,5	5	—	0	0,1	—	0	0,1	V
Low-Level, $V_{OL}$	—	0,10	10	—	0	0,1	—	—	—	
High-Level, $V_{OH}$	—	0,5	5	4,9	5	—	4,9	5	—	
	—	0,10	10	9,9	10	—	—	—	—	
Input Low Voltage, $V_{IL}$	0,5,4,5	—	5	—	—	1,5	—	—	1,5	
	1,9	—	10	—	—	3	—	—	—	
Input High Voltage, $V_{IH}$	0,5,4,5	—	5	3,5	—	—	3,5	—	—	
	1,9	—	10	7	—	—	—	—	—	
Output Low (Sink) Current, $I_{OL}$	0,4	0,5	5	1,8	2,2	—	1,8	2,2	—	mA
	0,5	0,10	10	3,6	4,5	—	—	—	—	
Output High (Source) Current, $I_{OH}$	4,6	0,5	5	-0,9	-1,1	—	-0,9	-1,1	—	
	9,5	0,10	10	-1,8	-2,2	—	—	—	—	
Input Current, $I_{IN}$	Any input	0,5	5	—	$\pm 0,1$	$\pm 1$	—	$\pm 0,1$	$\pm 1$	$\mu A$
		0,10	10	—	$\pm 0,1$	$\pm 1$	—	—	—	
3-State Output Leakage Current, $I_{OUT}$	0,5	0,5	5	—	$\pm 0,2$	$\pm 2$	—	$\pm 0,2$	$\pm 2$	
	0,10	0,10	10	—	$\pm 0,2$	$\pm 2$	—	—	—	
Operating Current, $I_{DD1} \dagger$	—	0,5	5	—	4	8	—	4	8	mA
	—	0,10	10	—	8	16	—	—	—	
Input Capacitance, $C_{IN}$	—	—	—	—	5	7,5	—	5	7,5	pF
Output Capacitance, $C_{OUT}$	—	—	—	—	10	15	—	10	15	

$\dagger$ Outputs open circuited; cycle time = 1  $\mu s$ .

\*Typical values are for  $T_A = 25^\circ C$  and nominal  $V_{DD}$ .

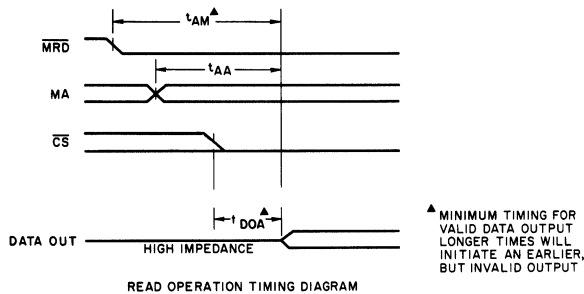
5

# CDP1824, CDP1824C

DYNAMIC ELECTRICAL CHARACTERISTICS at  $T_A = -40$  to  $+85^\circ\text{C}$ ,  $V_{DD} \pm 5\%$ ,  
 Input  $t_r, t_f = 10$  ns,  $C_L = 50$  pF,  $R_L = 200$  k $\Omega$ ; See Fig. 1.

CHARACTERISTIC	TEST CONDITIONS $V_{DD}$ (V)	LIMITS						UNITS
		CDP1824D CDP1824E			CDP1824CD CDP1824CE			
		Min.#	Typ.●	Max.	Min.#	Typ.●	Max.	
<b>Read Operation</b>								
Access Time From Address Change, $t_{AA}$	5	—	400	710	—	400	710	ns
	10	—	200	320	—	—	—	
Access Time From Chip Select, $t_{DOA}$	5	—	300	710	—	300	710	ns
	10	—	150	320	—	—	—	
Output Active From MRD, $t_{AM}$	5	—	300	710	—	300	710	ns
	10	—	150	320	—	—	—	

- Time required by a limit device to allow for the indicated function
- Time required by a typical device to allow for the indicated function. Typical values are for  $T_A = 25^\circ\text{C}$  and nominal  $V_{DD}$ .



92CS-34739

Fig. 1 - Read cycle timing diagram.

**Note:**

The dynamic characteristics and timing diagrams indicate maximum performance capability of the CDP1824. When used directly with the CDP1802 microprocessor, timing will be determined by the clock frequency and internal delays of the microprocessor.

The following general timing relationships will hold when the CDP1824 is used with the CDP1802 microprocessor:

$$t_{WW} = 2 t_c$$

$$t_{AH} = 1.0 t_c$$

$$\left. \begin{aligned} t_{AS} &= 4.5 t_c \\ t_{DH} &= 1.0 t_c \\ t_{DS} &= 5.5 t_c \end{aligned} \right\} \begin{array}{l} \text{Data transfers from} \\ \text{CDP1802 to memory} \end{array}$$

MRD occurs one clock period ( $t_c$ ) earlier than the address bits MA0-MA7.

$$\text{where } t_c = \frac{1}{\text{CDP1802 clock frequency}}$$

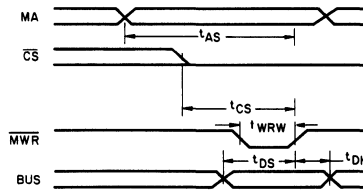
The CDP1824 is capable of operating at the maximum clock frequency of the CDP1802 microprocessor.

# CDP1824, CDP1824C

DYNAMIC ELECTRICAL CHARACTERISTICS at  $T_A = -40$  to  $+85^\circ\text{C}$ ,  $V_{DD} \pm 5\%$ ,  
 Input  $t_r, t_f = 10$  ns,  $C_L = 50$  pF,  $R_L = 200$  k $\Omega$ ; See Fig. 2.

CHARACTERISTIC	TEST CONDITIONS $V_{DD}$ (V)	LIMITS						UNIT
		CDP1824D CDP1824E			CDP1824CD CDP1824CE			
		Min.#	Typ.*	Max.	Min.#	Typ.*	Max.	
<b>Write Operation</b>								
Write Pulse Width, $t_{WRW}$	5	390	200	—	390	200	—	ns
	10	180	150	—	—	—	—	
Data Setup Time, $t_{DS}$	5	390	100	—	390	100	—	ns
	10	180	50	—	—	—	—	
Data Hold Time, $t_{DH}$	5	70	40	—	70	40	—	ns
	10	35	20	—	—	—	—	
Chip Select Setup Time, $t_{CS}$	5	425	210	—	425	210	—	ns
	10	215	110	—	—	—	—	
Address Setup Time, $t_{AS}$	5	640	500	—	640	500	—	ns
	10	390	300	—	—	—	—	

- \* Time required by a limit device to allow for the indicated function
- Time required by a typical device to allow for the indicated function. Typical values are for  $T_A = 25^\circ\text{C}$  and nominal  $V_{DD}$



WRITE OPERATION TIMING DIAGRAM  
92CS-34740

Fig. 2 - Write cycle timing diagram.

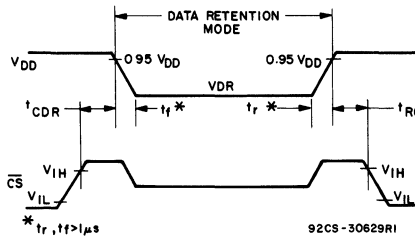


Fig. 3 - Low  $V_{DD}$  data retention waveforms and timing diagram.

# CDP1824, CDP1824C

DATA RETENTION CHARACTERISTICS at  $T_A = -40$  to  $+85^\circ\text{C}$ ; See Fig. 3.

CHARACTERISTIC	TEST CONDITIONS	$V_{DD}$ (V)	CDP1824		CDP1824C		UNITS
			Min.	Max.	Min.	Max.	
			Data Retention Voltage, $V_{DR}$	—	2.5	—	
Data Retention Quiescent Current, $I_{DD}$	$V_{DR} = 2.5\text{ V}$	—	—	10	—	40	$\mu\text{A}$
Chip Deselect to Data Retention Time, $t_{CDR}$	$V_{DR} = 2.5\text{ V}$	5 10	600 300	— —	600 —	— —	ns
Recovery to Normal Operation Time, $t_{RC}$	$V_{DR} = 2.5\text{ V}$	5 10	600 300	— —	600 —	— —	

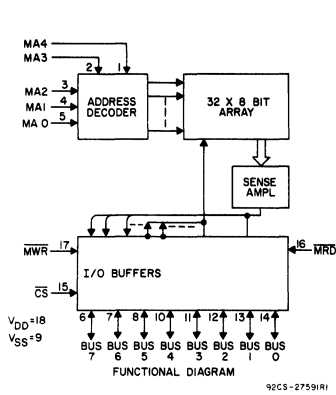


Fig. 4 - Functional diagram.

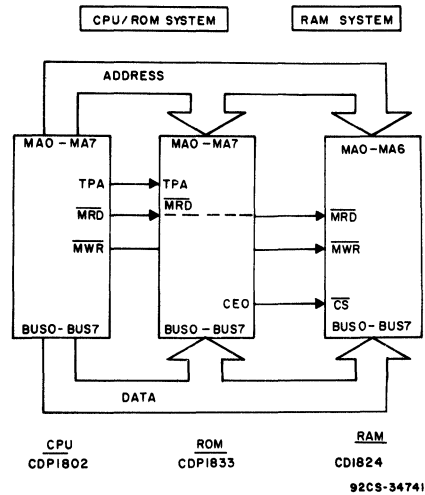


Fig. 5 - CDP1824 (128 x 8) minimum system (128 x 8)